



SLPS199A - AUGUST 2009 - REVISED APRIL 2010

N-Channel NexFET[™] Power MOSFET

Check for Samples: CSD16413Q5A

FEATURES

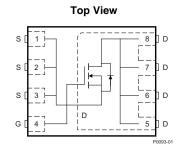
- Ultra Low Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5mm × 6mm Plastic Package

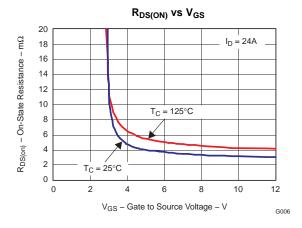
APPLICATIONS

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Control or Synchronous FET Applications

DESCRIPTION

The NexFET[™] power MOSFET has been designed to minimize losses in power conversion applications.





PRODUCT SUMMARY

V _{DS}	Drain to Source Voltage 25			V
Qg	Gate Charge Total (4.5V)	9	nC	
Q _{gd}	Gate Charge Gate to Drain	2.5	nC	
D	Drain to Source On Resistance	$V_{GS} = 4.5V$	4.1	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 10V$	3.1	mΩ
V _{GS(th)}	Threshold Voltage 1.6		V	

ORDERING INFORMATION

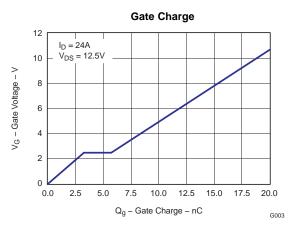
Device	Package	Media	Qty	Ship
CSD16413Q5A	SON 5 × 6 Plastic Package	13-inch reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5°C unless otherwise stated	VALUE	UNIT
V _{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+16 / -12	V
	Continuous Drain Current, T _C = 25°C	100	А
ID	Continuous Drain Current ⁽¹⁾	24	А
I _{DM}	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	156	А
PD	Power Dissipation ⁽¹⁾	3.1	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D = 46A$, L = 0.1mH, $R_G = 25\Omega$	106	mJ

(1) $R_{\theta JA} = 41^{\circ}C/W$ on $1in^2$ Cu (2 oz.) on 0.060" thick FR4 PCB.

(2) Pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	haracteristics				¥	
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	25			V
I _{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$			1	μA
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +16/-12V$			100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.2	1.6	1.9	V
D	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 24A$		4.1	5.6	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 10V, I_{D} = 24A$		3.1	3.9	mΩ
g _{fs}	Transconductance	$V_{DS} = 15V, I_{D} = 24A$		95		S
Dynamic	Characteristics	· · · · · · · · · · · · · · · · · · ·				
C _{ISS}	Input Capacitance			1370	1780	pF
C _{OSS}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V f = 1MHz$		1060	1380	pF
C _{RSS}	Reverse Transfer Capacitance			84	109	pF
R _g	Series Gate Resistance			0.9	1.8	Ω
Qg	Gate Charge Total (4.5V)			9	11.7	nC
Q _{gd}	Gate Charge Gate to Drain	V 12 5V 1 24A		2.5		nC
Q _{gs}	Gate Charge Gate to Source	V _{DS} = 12.5V, I _D = 24A		3.5		nC
Qg(th)	Gate Charge at Vth			2.2		nC
Q _{OSS}	Output Charge	$V_{DS} = 13.1V, V_{GS} = 0V$		21		nC
t _{d(on)}	Turn On Delay Time			9.1		ns
t _r	Rise Time	V _{DS} = 12.5V, V _{GS} = 4.5V I _D = 24A		15.9		ns
t _{d(off)}	Turn Off Delay Time	$R_G = 5\Omega$		10.7		ns
t _f	Fall Time			5.7		ns
Diode Cl	haracteristics				¥	
V _{SD}	Diode Forward Voltage	$I_{S} = 24A, V_{GS} = 0V$		0.85	1	V
Q _{rr}	Reverse Recovery Charge	$V_{DD} = 13.1V, I_F = 24A, di/dt = 300A/\mu s$		32		nC
t _{rr}	Reverse Recovery Time	V _{DD} = 13.1V, I _F = 24A, di/dt = 300A/µs		28		ns

THERMAL CHARACTERISTICS

($T_A = 25^{\circ}C$ unless otherwise stated)

	PARAMETER	MIN	TYP	MAX	UNIT
R $_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾			2.6	°C/W
R $_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾ ⁽²⁾			51	°C/W

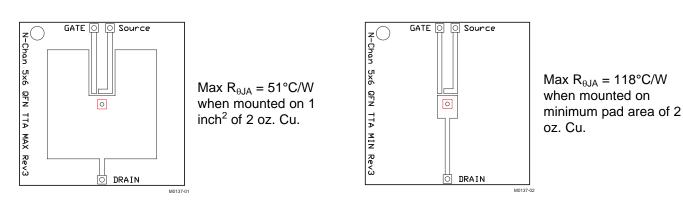
(1) $R_{\theta JC}$ is determined with the device mounted on a 1 inch square 2 oz. Cu pad on a 1.5 x 1.5 in .060 inch thick FR4 board. $R_{\theta JC}$ is specified by design while $R_{\theta JA}$ is determined by the user's board design.

(2) Device mounted on FR4 Material with 1 inch² of 2 oz. Cu.



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TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

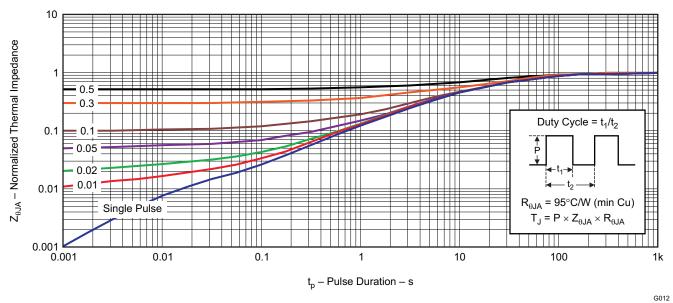
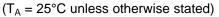


Figure 1. Transient Thermal Impedance







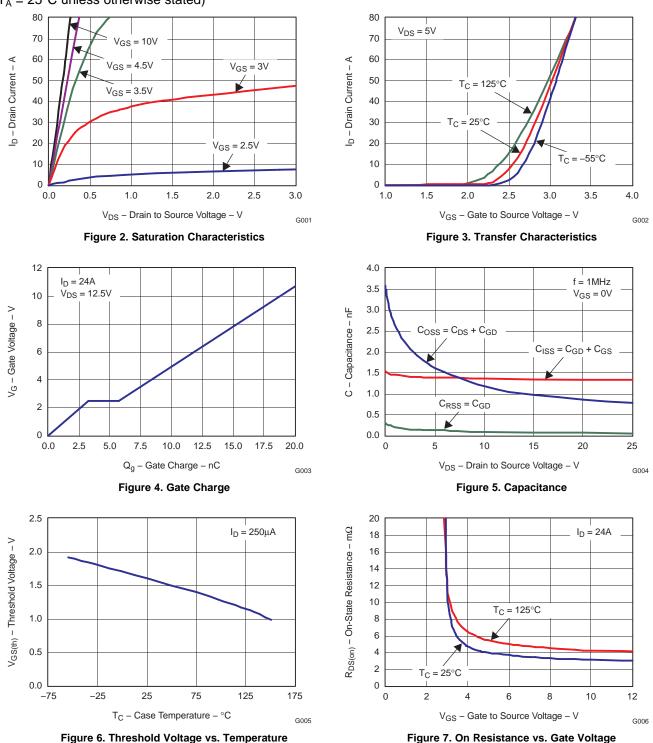
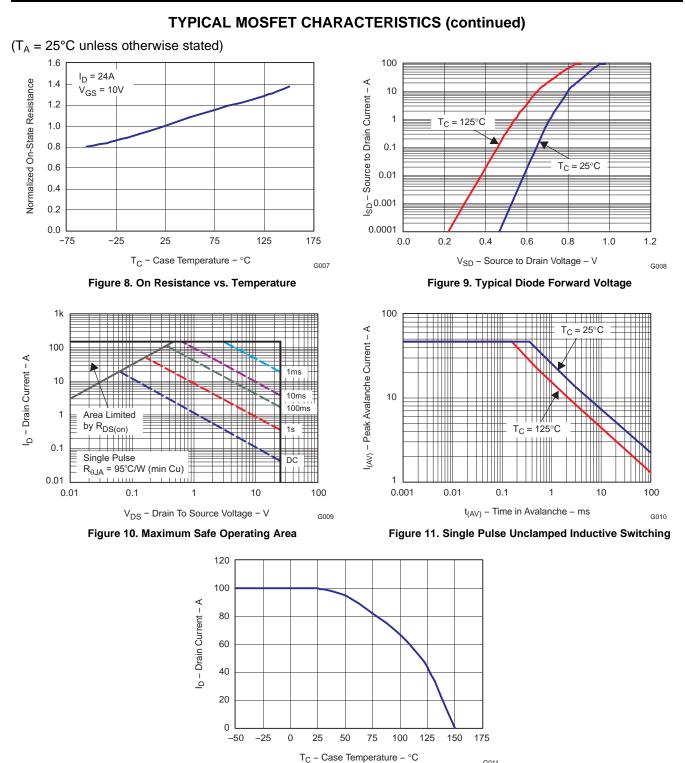


Figure 7. On Resistance vs. Gate Voltage



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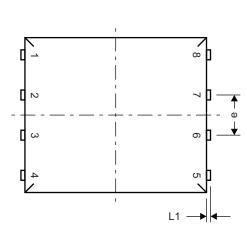
Figure 12. Maximum Drain Current vs. Temperature

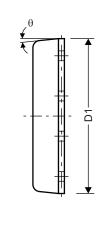
TEXAS INSTRUMENTS

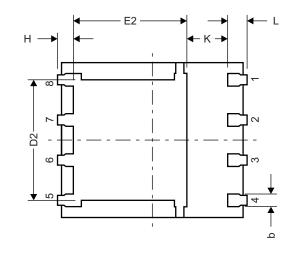
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MECHANICAL DATA

Q5A Package Dimensions



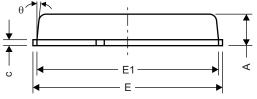




Top View

Side View

Bottom View



Front View

M0135-01

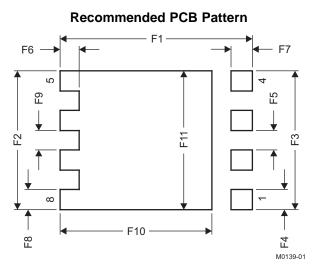
DIM		MILLIMETERS							
	MIN	NOM	MAX						
А	0.90	1.00	1.10						
b	0.33	0.41	0.51						
С	0.20	0.25	0.30						
D1	4.80	4.90	5.00						
D2	3.61	3.81	3.96						
E	5.90	6.00	6.10						
E1	5.70	5.75	5.80						
E2	3.38	3.58	3.78						
е	1.27 BSC								
Н	0.41 0.51		0.61						
К	1.10								
L	0.51	0.61	0.71						
L1	0.06	0.13	0.20						
θ	0°		12°						



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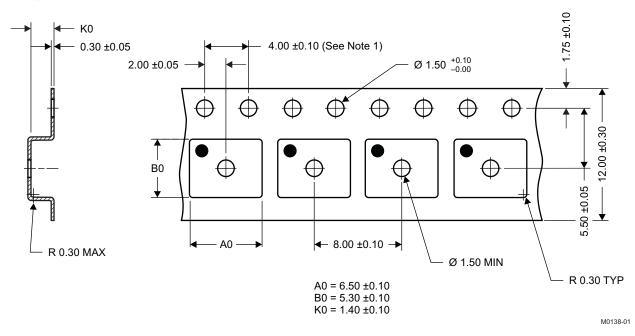
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DIM	MILLIM	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.038	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5A Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible

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REVISION HISTORY

Cł	hanges from Original (August 2009) to Revision A	Page
•	Deleted the Package Marking Information section	7



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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal	
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Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16413Q5A	SON	DQJ	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

8-Apr-2013



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD16413Q5A	SON	DQJ	8	2500	340.0	340.0	38.0

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